TOSHIBA Photocoupler IRED & Photo-Transistor

# **TLP331, TLP332**

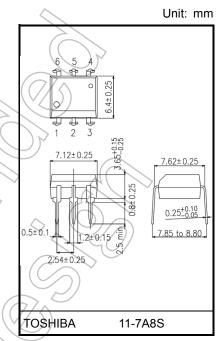
**Programmable Controllers** AC/DC-Input Module **Telecommunication** 

The TOSHIBA TLP331 and TLP332 consist of an infrared emitting diode optically coupled to a photo-transistor in a six lead plastic DIP package. This photocoupler provides the unique feature of high current transfer ratio at both low output voltage and low input current. This makes it ideal for use in low power logic circuits, telecommunications equipment and portable electronics isolation applications.

TLP332 has no-base internal connection for high-EMI environments.

- Collector-emitter voltage: 55 V (min)
- Isolation voltage: 5000 Vrms (min)
- UL-recognized: UL 1577, File No.E67349
- cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

Current transfer ratio



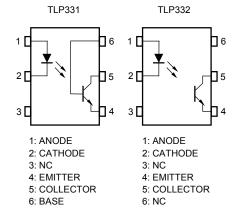
Weight: 0.4 g (typ.)

		Curr			
	Classification (Note 1)	Ta =	25°C	Ta = -25 to 75°C	Marking of
		I <sub>F</sub> = 1 mA V <sub>CE</sub> = 0.5V	I <sub>F</sub> = 0.5 mA V <sub>CE</sub> = 1.5V	l <sub>F</sub> = 1 mA V <sub>CE</sub> = 0.5V	Classification
	Rank BV	200%	100%	100%	BV
	Standard	100%	50%	50%	BV, blank

Note 1: ex. Standard: TLP331 Rank BV: TLP331(BV)

Note: Application type name for certification test, please use standard product type name, i.e. TLP331(BV): TLP331

## Pin Configurations (top view)



Start of commercial production 1986-03

#### **Absolute Maximum Ratings (Ta = 25°C)**

	Characteristics	Symbol	Rating	Unit
	Forward current	lF	50	mA
	Forward current derating (Ta ≥ 39°C)	ΔI <sub>F</sub> /°C	-0.7	mA/°C
	Peak forward current (100 µs pulse, 100 pps)	lFP	1	Α
LED	Reverse Voltage	VR	5	<
	Diode power dissipation	PD	50	mW
	Diode power dissipation derating (Ta >39 °C)	ΔP <sub>D</sub> /°C	-0.58	mW/°C
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	VCEO	55	٧
	Collector-base voltage (TLP331)	Vсво	80	٧
	Emitter-collector voltage	VECO	7	V
Detector	Emitter-base voltage (TLP331)	VEBO	7	N
Dete	Collector current		50	mA
	Power dissipation	PC	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔPc/°C	-1,5	mW/°C
	Junction temperature	Тј	125	°C
Stor	age temperature range	T <sub>stg</sub>	-55 to 125	°C
Оре	rating temperature range	T <sub>opr</sub>	-55 to 100	°C
Lead	d soldering temperature (10 s)	Tsol	260	°C
Tota	al package power dissipation	RI	250	mW
Tota	al package power dissipation derating (Ta ≥ 25°C)	PT/°C	-2.5	mW/°C
Isola	ation voltage (AC, 60 s, RH ≤ 60 %) (Note 1)	BVs	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

#### **Recommended Operating Conditions**

Characteristics	Symbol	Min	Тур.	Max	Unit
Supply voltage	Vcc	_	5	25	V
Forward current	√ lF	_	1.6	25	mA
Collector current	IC	_	1	10	mA
Operating temperature	T <sub>opr</sub>	-25	_	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.



#### **Electrical Characteristics (Ta = 25°C)**

	Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	VF	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μA
	Capacitance	Ст	V = 0 V, f = 1 MHz	\  -	30	-	pF
	Collector-emitter breakdown voltage	V(BR)CEO	IC = 0.5 mA	55		١	V
	Emitter-collector breakdown voltage	V <sub>(BR)ECO</sub>	I <sub>E</sub> = 0.1 mA	7		)\'\ -	V
	Collector-base breakdown voltage (TLP331)	V <sub>(BR)</sub> CBO	I <sub>C</sub> = 0.1 mA	80/	) \ -	ı	V
_	Emitter-base breakdown voltage (TLP331)	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 0.1 mA	7	/_	-	V
Detector	Callegtor dark ourrent	ICEO	V <sub>CE</sub> = 24 V	7	10	100	nA
Det	Collector dark current		V <sub>CE</sub> = 24 V, Ta = 85 °C	)	2	50	μA
	Collector dark current (TLP331)	I <sub>CER</sub>	V <sub>CE</sub> = 24 V, Ta = 85 °C R <sub>BE</sub> = 1 MΩ		0.5	10	μA
	Collector dark current (TLP331)	I <sub>CBO</sub>	V <sub>CB</sub> = 10 V	$\Diamond$	0.1		nA
	DC forward current gain (TLP331)	hFE	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 mA		1000	16//	_
	Capacitance (collector to emitter)	CCE	V = 0 V , f = 1 MHz	+	12	)	pF

### Coupled Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	Ic/IF	IF = 1 mA, V <sub>CE</sub> = 0.5 V	100	_	1200	%
Current transfer fatto		Rank BV	200	_	1200	
Low input CTR	IC/IF(low)	IF = 0.5 mA, VCE = 1.5 V	50	-	_	%
Low Input CTR		Rank BV	100	-	_	70
Base photo-current (TLP331)	IPB	IF = 1 mA, V <sub>CB</sub> = 5 V	_	10	1	μΑ
	()	IC = 0.5 mA, IF = 1 mA	_	_	0.4	
Collector-emitter saturation voltage	VCE(sat)	IC = 1 mA, IF = 1 mA	_	0.2	_	V
		Rank BV	_	_	0.4	

#### Coupled Electrical Characteristics (Ta = 25 to 75°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Current transfer ratio	. /	IC/IF	I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 0.5 V	50	-	-	%
Current transfer fatto	$\langle \rangle$	1C/IF	Rank BV	100	1	l	70
Low input CTR	>/<	I <sub>C</sub> /I <sub>F(low)</sub>	I <sub>F</sub> = 0.5 mA, V <sub>CE</sub> = 1.5 V	_	50	ı	%
LOW INDUCTION	~ \ \	iC/iF(low)	Rank BV	_	100	1	/0



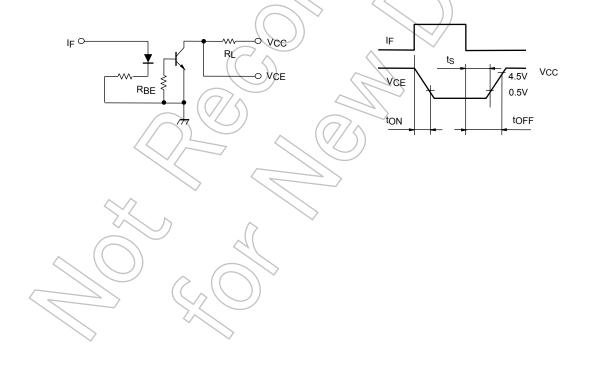
### Isolation Characteristics (Ta = 25°C)

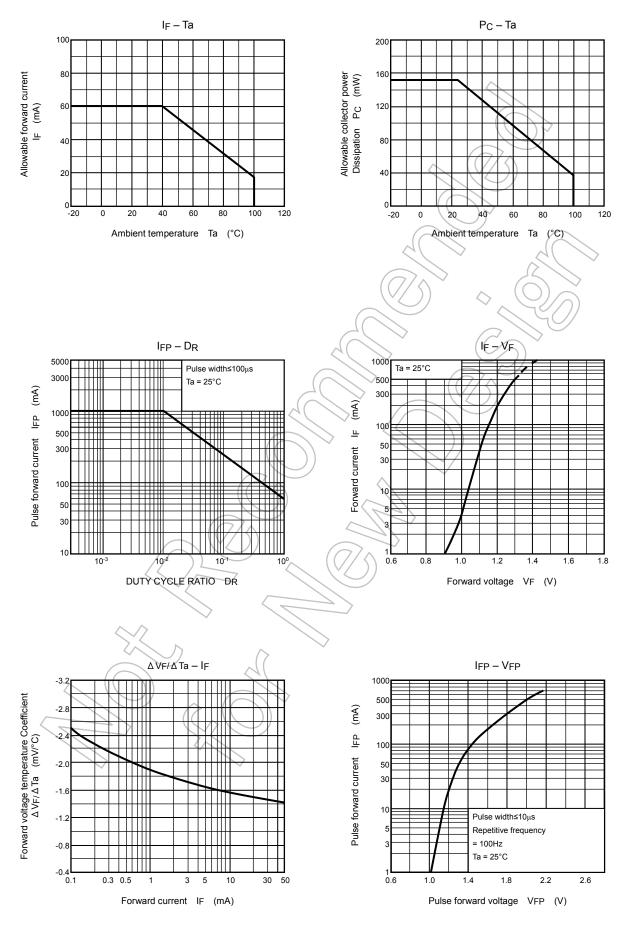
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	Cs	V <sub>S</sub> = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	Rs	V = 500 V, RH ≤ 60 %	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	BVs	AC, 60 s	5000	/	_	Vrms

#### **Switching Characteristics (Ta = 25°C)**

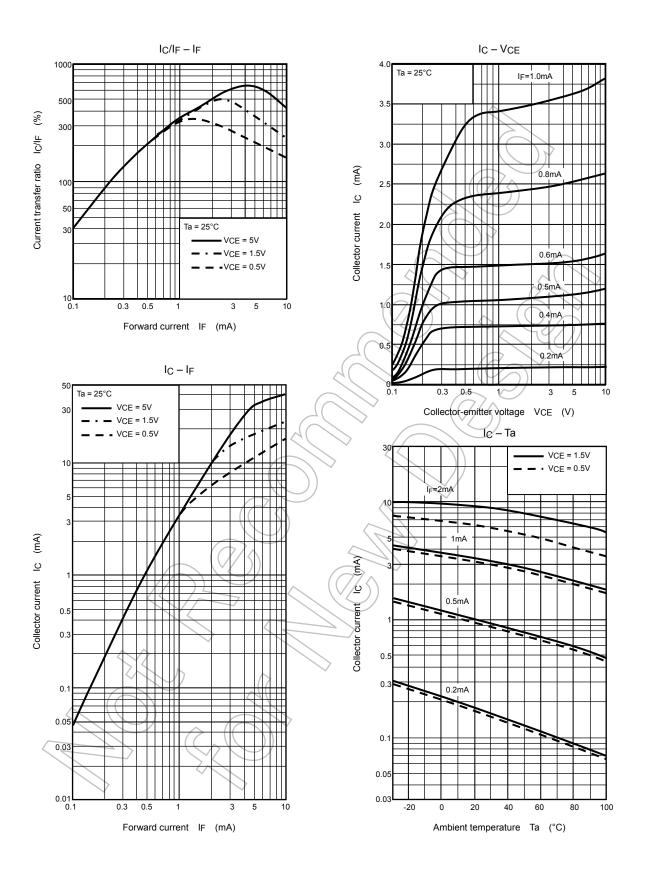
Characteristics	Symbol	Test Condition Min Typ. Max Unit
Rise time	t <sub>r</sub>	8 -
Fall time	tf	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA
Turn-on time	ton	R <sub>L</sub> = 100 Ω
Turn-off time	t <sub>off</sub>	- 8 -
Turn-on time	ton	R <sub>L</sub> = 4.7 kΩ (Fig.1) — 10
Storage time	ts	R <sub>BE</sub> = OPEN
Turn-off time	toff	V <sub>CC</sub> = 5 V, I <sub>E</sub> = 1.6 mA _ 300
Turn-on time	ton	$R_L = 4.7 \text{ k}\Omega$ (Fig.1)
Storage time	ts	$R_{BE}$ = 470 kΩ (TLP331) — 30 — µs
Turn-off time	toff	V <sub>CC</sub> = 5 V, I <sub>F</sub> ⇒ 1.6 mA

Fig. 1 Switching time test circuit

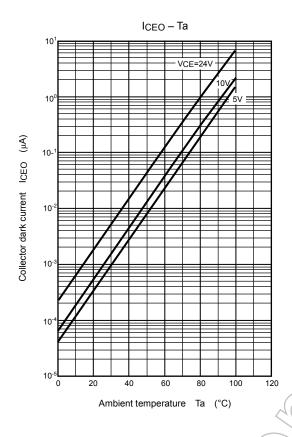


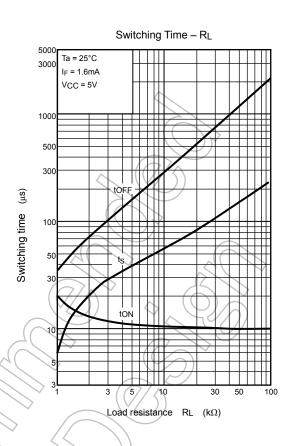


NOTE: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



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